



2SB1016

PNP EPITAXIAL SILICON TRANSISTOR

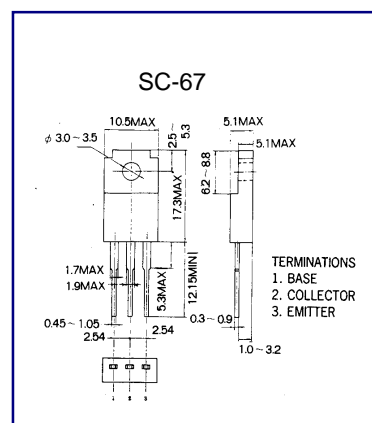
POWER AMPLIFIER

VERTICAL DEFLECTION OUTPUT

- Complement to 2SD1407

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-100	V
Collector-Emitter Voltage	V_{CE0}	-100	V
Emitter-Base voltage	V_{EB0}	-5	V
Collector Current (DC)	I_C	-3	A
Collector Dissipation ($T_c=25^\circ\text{C}$)	P_C	25	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-50~150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -150\text{V}, I_E = 0$			-10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-10	μA
DC Current Gain	h_{FE1}	$V_{CE} = -5.0\text{V}, I_C = -1.0\text{A}$		100		
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -4\text{A}, I_B = -0.4\text{mA}$			-2.0	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}$		60		MHZ